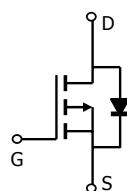
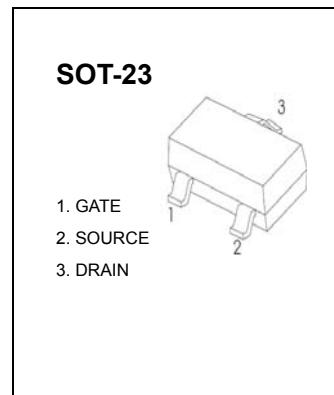


A03401 P-Channel Enhancement Mode Field Effect Transistor

FEATURE

- High dense cell design for extremely low $R_{DS(ON)}$.
- Exceptional on-resistance and maximum DC current capability


MARKING: A19T

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-4.2	A
Power Dissipation	P_D	350	mW
Thermal Resistance from Junction to Ambient (t<5s)	$R_{\theta JA}$	357	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Electrical characteristics ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off characteristics						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = -250\mu\text{A}$	-30			V
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = -24\text{V}, V_{\text{GS}} = 0\text{V}$			-1	μA
Gate-source leakage current	I_{GSS}	$V_{\text{GS}} = \pm 12\text{V}, V_{\text{DS}} = 0\text{V}$			± 100	nA
On characteristics						
Drain-source on-resistance (note 1)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = -10\text{V}, I_{\text{D}} = -4.2\text{A}$			65	$\text{m}\Omega$
		$V_{\text{GS}} = -4.5\text{V}, I_{\text{D}} = -4\text{A}$			75	$\text{m}\Omega$
		$V_{\text{GS}} = -2.5\text{V}, I_{\text{D}} = -1\text{A}$			90	$\text{m}\Omega$
Forward transconductance (note 1)	g_{FS}	$V_{\text{DS}} = -5\text{V}, I_{\text{D}} = -5\text{A}$	7			S
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = -250\mu\text{A}$	-0.7		-1.3	V
Dynamic characteristics (note 2)						
Input capacitance	C_{iss}	$V_{\text{DS}} = -15\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		954		pF
Output capacitance	C_{oss}			115		pF
Reverse transfer capacitance	C_{rss}			77		pF
Switching characteristics (note 2)						
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{GS}} = -10\text{V}, V_{\text{DS}} = -15\text{V}, R_{\text{L}} = 3.6\Omega, R_{\text{GEN}} = 6\Omega$			6.3	ns
Turn-on rise time	t_{r}				3.2	ns
Turn-off delay time	$t_{\text{d}(\text{off})}$				38.2	ns
Turn-off fall Time	t_{f}				12	ns
Drain-source diode characteristics and maximum ratings						
Diode forward voltage (note 1)	V_{SD}	$I_{\text{S}} = -1\text{A}, V_{\text{GS}} = 0\text{V}$			-1	V

Note :

1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
2. These parameters have no way to verify.